## BAW56M3T5G

# **Dual Switching Diode Common Anode**

The BAW56M3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for switching applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

## **MAXIMUM RATINGS** (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	75	Vdc
Forward Current	ΙF	200	mAdc
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	265 2.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	640 5.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

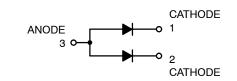
- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



## ON Semiconductor®

http://onsemi.com

# 70 V DUAL COMMON ANODE SWITCHING DIODE



## MARKING DIAGRAM



AN = Specific Device Code M = Date Code

### **ORDERING INFORMATION**

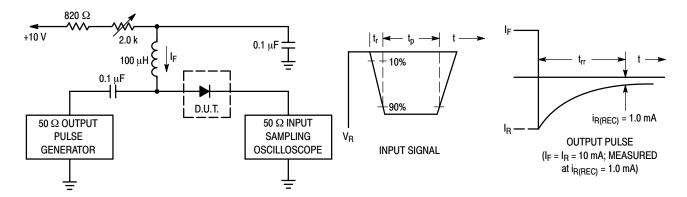
Device	Package	Shipping <sup>†</sup>
BAW56M3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## BAW56M3T5G

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Each Diode)

Characteristic		Symbol	Min	Max	Unit
Reverse Breakdown Voltage	(I <sub>(BR)</sub> = 100 μA)	V <sub>(BR)</sub>	70	-	V
Reverse Voltage Leakage Current	(V <sub>R</sub> = 25 V, T <sub>J</sub> = 150°C) (V <sub>R</sub> = 70 V) (V <sub>R</sub> = 70 V, T <sub>J</sub> = 150°C)	I <sub>R</sub>	- - -	30 2.5 50	μΑ
Diode Capacitance	(V <sub>R</sub> = 0 V, f = 1.0 MHz)	C <sub>D</sub>	-	2.0	pF
Forward Voltage	(I <sub>F</sub> = 1.0 mA) (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 50 mA) (I <sub>F</sub> = 150 mA)	V <sub>F</sub>	- - - -	715 855 1000 1250	mV
Reverse Recovery Time $(I_F = I_R = 10 \text{ mA}, I_{R(REC)} = 1.0 \text{ mA}) \text{ (Figure 1)}$	R <sub>L</sub> = 100 Ω	t <sub>rr</sub>	-	6.0	ns



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (IF) of 10 mA.

Figure 1. Recovery Time Equivalent Test Circuit

<sup>2.</sup> Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.

<sup>3.</sup> t<sub>p</sub> » t<sub>rr</sub>

## BAW56M3T5G

## **Curves Applicable to Each Cathode**

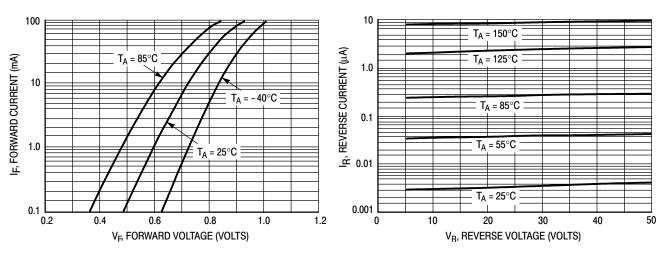


Figure 2. Forward Voltage

Figure 3. Leakage Current

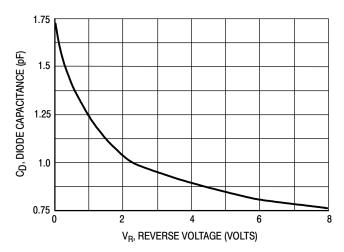


Figure 4. Capacitance



MILL IMETERS

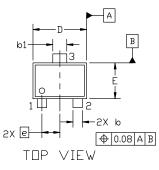


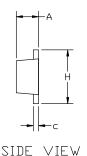
### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

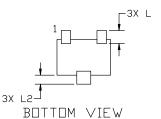
**DATE 24 JAN 2024** 

#### NOTES:

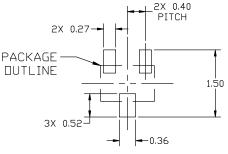
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
А	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
E	0.75	0.80	0.85	
е	0.40 BSC			
Н	1.15	1.20	1.25	
L	0.29 REF			
L2	0.15	0.20	0.25	



RECOMMENDED MOUNTING FUUTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	<ol><li>CATHODE</li></ol>	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

DESCRIPTION	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1	
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